

Silicon NPN Darlington Power Transistors

2SD2495

DESCRIPTION

- With TO-220F package
- Complement to type 2SB1626

APPLICATIONS

- For audio, series regulator and general purpose applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

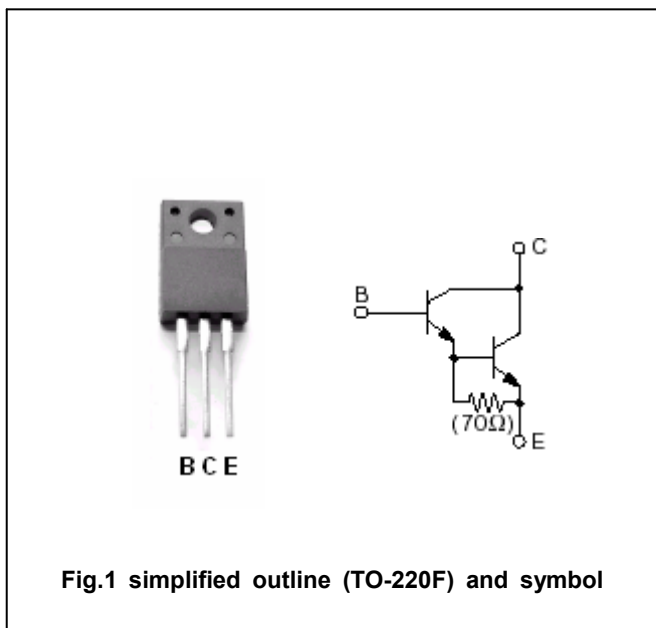


Fig.1 simplified outline (TO-220F) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	110	V
V _{CEO}	Collector-emitter voltage	Open base	110	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		6	A
I _B	Base current		1	A
P _C	Collector dissipation	T _C =25°C	30	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=50mA ; I_B=0$	110			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=5A ; I_B=5mA$			2.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=5A ; I_B=5mA$			3.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=110V ; I_E=0$			0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V ; I_C=0$			0.1	mA
h_{FE}	DC current gain	$I_C=5A ; V_{CE}=4V$	5000			
f_T	Transition frequency	$I_C=0.5A ; V_{CE}=12V$		60		MHz
C_{OB}	Collector output capacitance	$f=1MHz ; V_{CB}=10V$		55		pF

Switching times

t_{on}	Turn-on time	$I_C=5A ; I_{B1}=-I_{B2}=5mA$ $V_{CC}=30V , R_L=6\Omega$		0.8		μs
t_s	Storage time			6.2		μs
t_f	Fall time			1.1		μs

◆ h_{FE} Classifications

O	P	Y
5000-12000	6500-20000	15000-30000

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PACKAGE OUTLINE

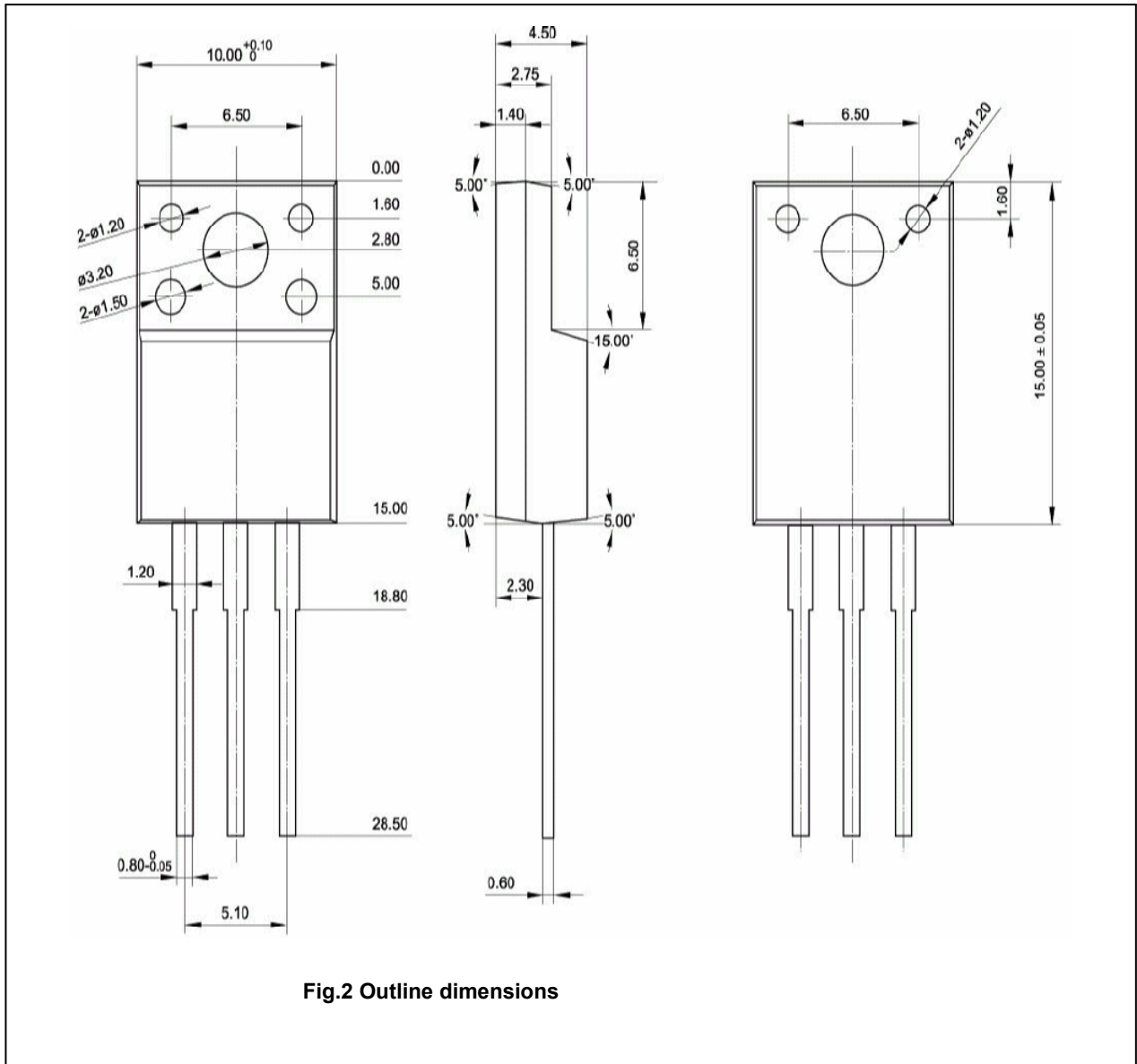


Fig.2 Outline dimensions